



SPC4533

N & P Pair Enhancement Mode MOSFET

DESCRIPTION

The SPC4533 is the N- and P-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

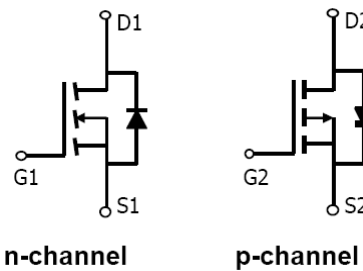
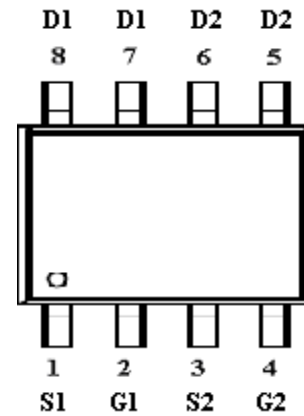
FEATURES

- ◆ N-Channel
30V/8.0A, $R_{DS(ON)} = 18\Omega @ V_{GS} = 10V$
30V/6.0A, $R_{DS(ON)} = 36m\Omega @ V_{GS} = 4.5V$
- ◆ P-Channel
-30V/-6.0A, $R_{DS(ON)} = 36m\Omega @ V_{GS} = -10V$
-30V/-4.0A, $R_{DS(ON)} = 65m\Omega @ V_{GS} = -4.5V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOP – 8P package design

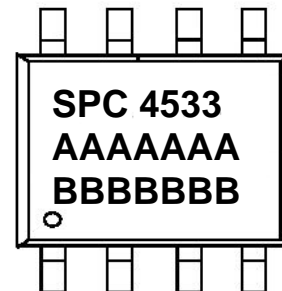
APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION(SOP – 8P)



PART MARKING



AAAAAAA : Lot NO.
BBBBBBB : Date Code



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PIN DESCRIPTION

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	S2	Source 2
4	G2	Gate 2
5	D2	Drain 2
6	D2	Drain 2
7	D1	Drain 1
8	D1	Drain 1

ORDERING INFORMATION

Part Number	Package	Part Marking
SPC4533S8RGB	SOP- 8P	SPC4533

※ SPC4533S8RGB : 13" Tape Reel ; Pb – Free ; Halogen - Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical		Unit
		N-Channel	P-Channel	
Drain-Source Voltage	V _{DSS}	30	-30	V
Gate –Source Voltage	V _{GSS}	±20	±20	V
Continuous Drain Current(T _J =150°C)	I _D	TA=25°C	-6.0	A
		TA=70°C	-4.0	
Pulsed Drain Current	I _{DM}	30	-30	A
Power Dissipation	P _D	2.0		W
Operating Junction Temperature	T _J	-55/150		°C
Storage Temperature Range	T _{STG}	-55/150		°C
Thermal Resistance-Junction to Ambient	R _{θJA}	T ≤ 10sec	52	°C/W
		Steady State	80	



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N-CH Electrical Characteristics@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=8A$	-	-	18	m Ω
		$V_{GS}=4.5V, I_D=6A$	-	-	36	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=8A$	-	13	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V$	-	-	1	μA
	Drain-Source Leakage Current ($T_j=70^\circ\text{C}$)	$V_{DS}=24V, V_{GS}=0V$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 30	μA
Q_g	Total Gate Charge ²	$I_D=8A$	-	6.5	10.5	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=15V$	-	2.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	3.3	-	nC
$t_{d(on)}$	Turn-on Delay Time ²	$V_{DS}=15V$	-	8	-	ns
t_r	Rise Time	$I_D=1A$	-	6	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	17	-	ns
t_f	Fall Time	$R_D=15\Omega$	-	6	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	540	860	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	150	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	90	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=1.5A, V_{GS}=0V$	-	-	1.3	V
t_{rr}	Reverse Recovery Time ²	$I_S=8A, V_{GS}=0V$	-	20	-	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	12	-	nC



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N & P Pair Enhancement Mode MOSFET

P-CH Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-6A	-	-	36	mΩ
		V _{GS} =-4.5V, I _D =-4A	-	-	65	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-3	V
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-6A	-	9.4	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V	-	-	-1	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =-24V, V _{GS} =0V	-	-	-25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±30	uA
Q _g	Total Gate Charge ²	I _D =-6A	-	9	14.5	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-15V	-	2.5	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	5.5	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =-15V	-	8	-	ns
t _r	Rise Time	I _D =-1A	-	9.5	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =-10V	-	20	-	ns
t _f	Fall Time	R _D =15Ω	-	20	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	500	800	pF
C _{oss}	Output Capacitance	V _{DS} =-25V	-	180	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	135	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =-1.5A, V _{GS} =0V	-	-	-1.3	V
t _{rr}	Reverse Recovery Time ²	I _S =-6A, V _{GS} =0V	-	25	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=-100A/μs	-	17	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board , t ≤10sec ; 135°C/W when mounted on min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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N-Channel

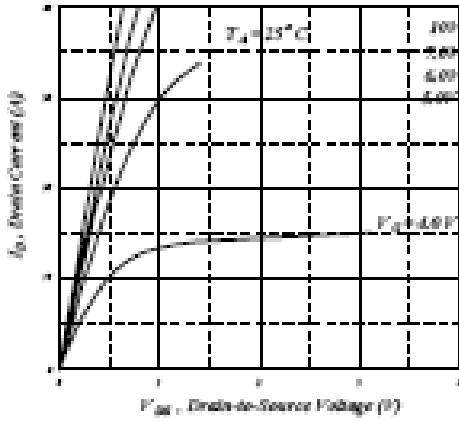


Fig 1. Typical Output Characteristics

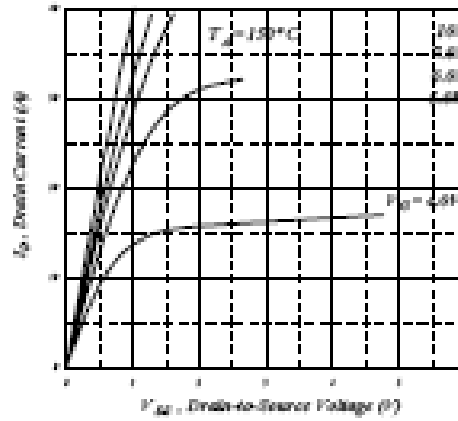


Fig 2. Typical Output Characteristics

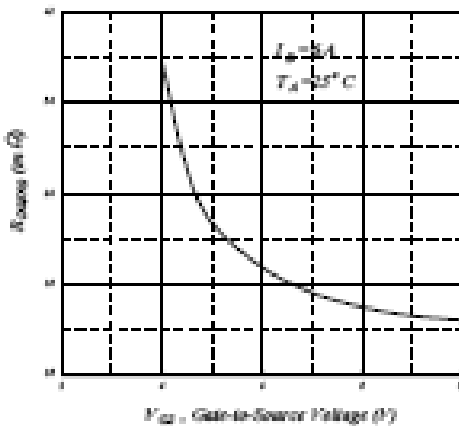


Fig 3. On-Resistance v.s. Gate Voltage

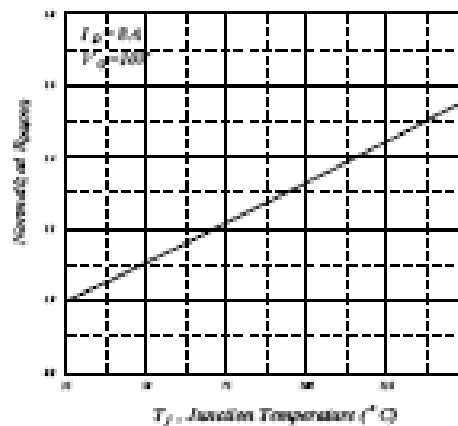


Fig 4. Normalized On-Resistance v.s. Junction Temperature

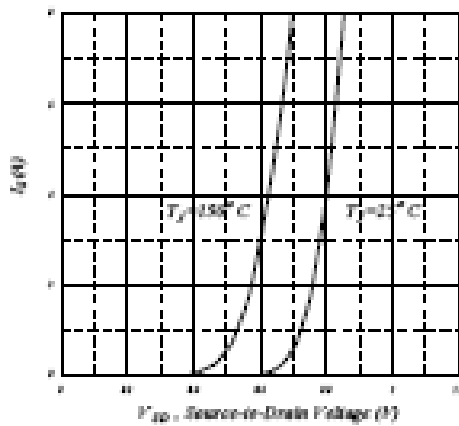


Fig 5. Forward Characteristic of Reverse Diode

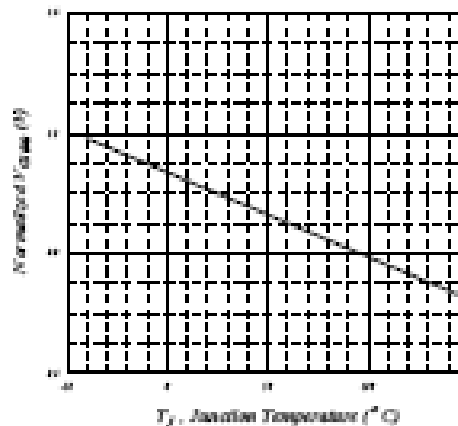


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



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N-Channel

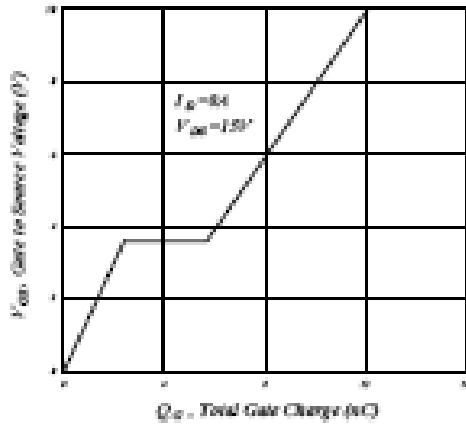


Fig 7. Gate Charge Characteristics

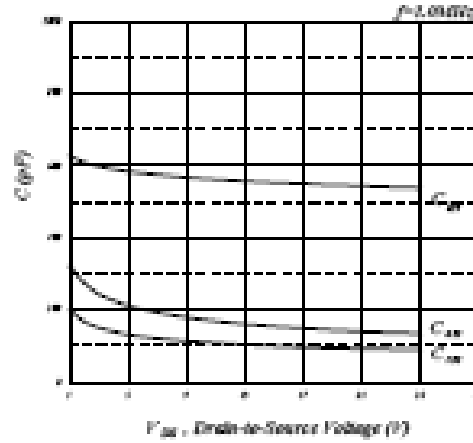


Fig 8. Typical Capacitance Characteristics

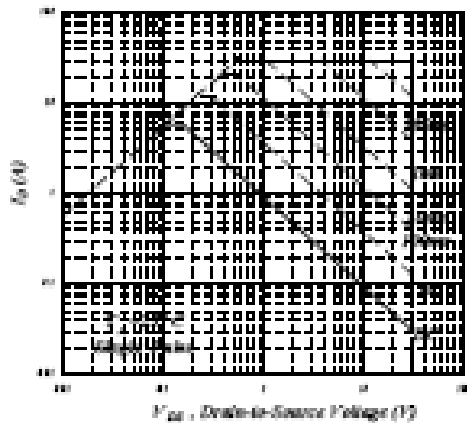


Fig 9. Maximum Safe Operating Area

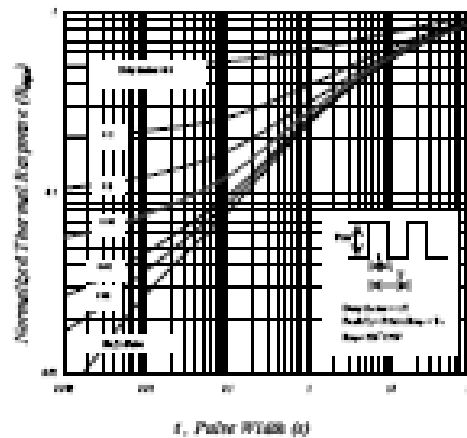


Fig 10. Effective Transient Thermal Impedance

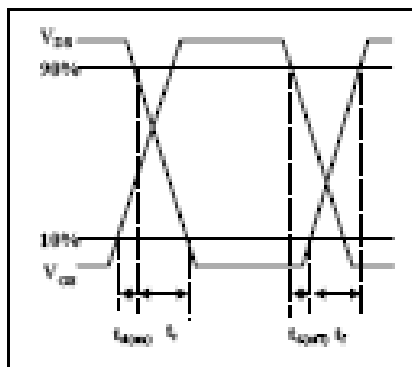


Fig 11. Switching Time Waveform

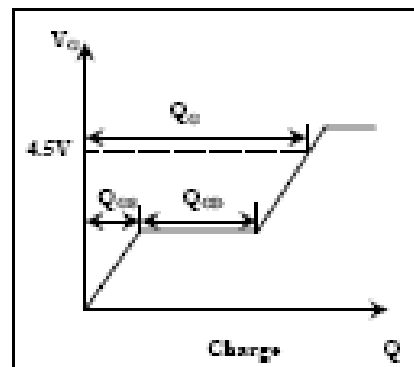


Fig 12. Gate Charge Waveform



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P-Channel

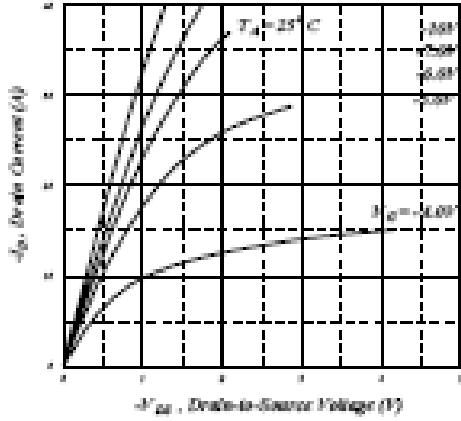


Fig 1. Typical Output Characteristics

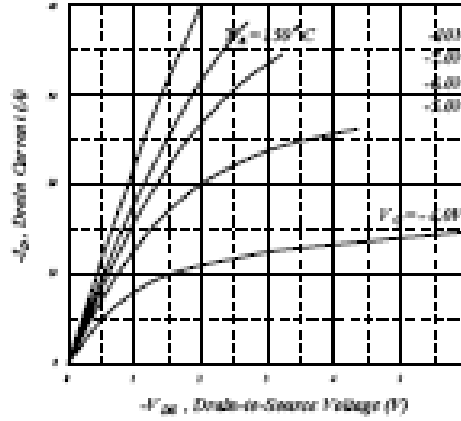


Fig 2. Typical Output Characteristics

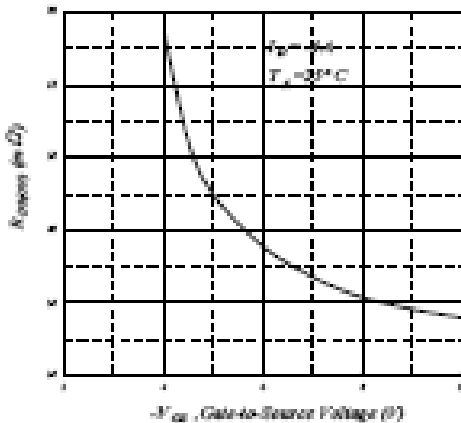


Fig 3. On-Resistance v.s. Gate Voltage

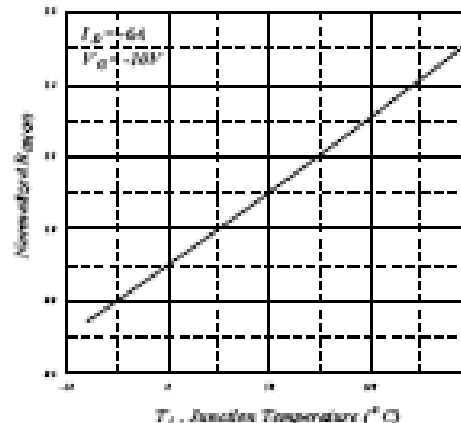


Fig 4. Normalized On-Resistance v.s. Junction Temperature

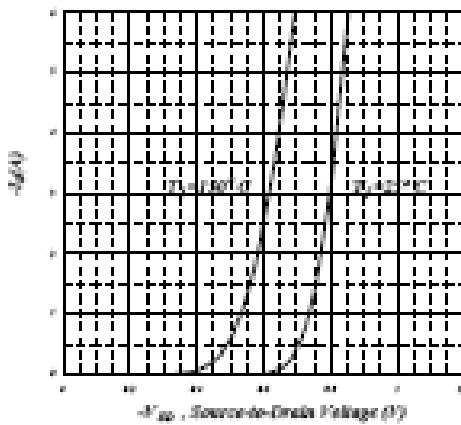


Fig 5. Forward Characteristic of Reverse Diode

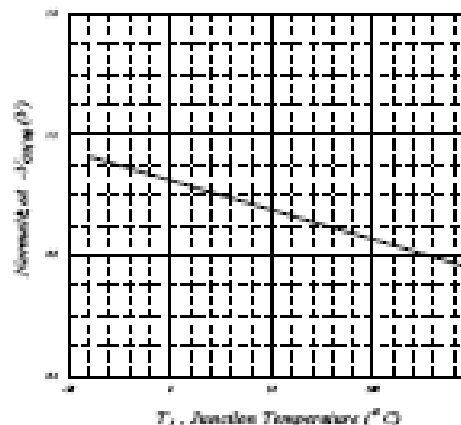


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



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P-Channel

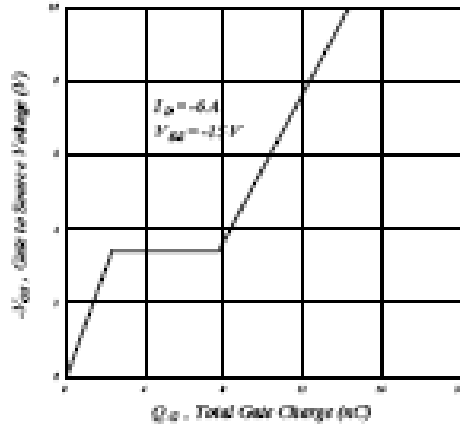


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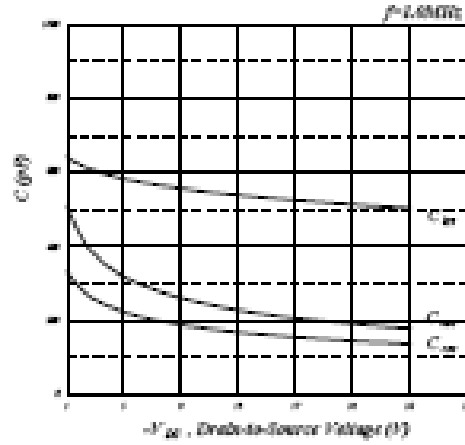


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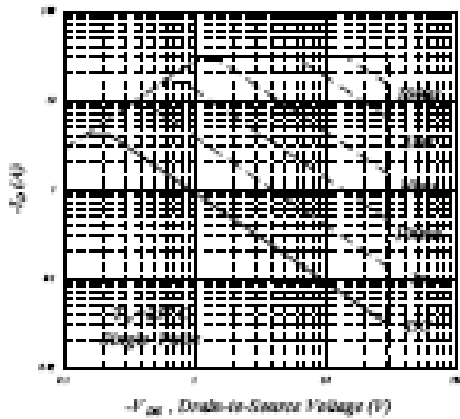


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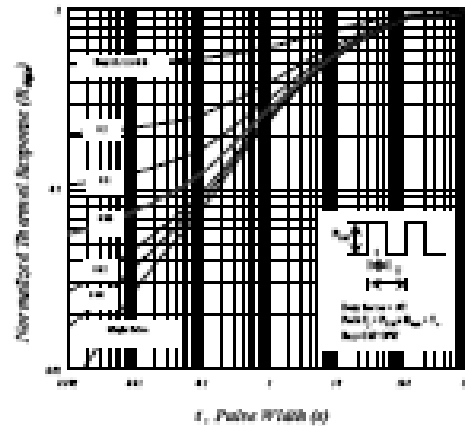


Fig 10. Effective Transient Thermal Impedance

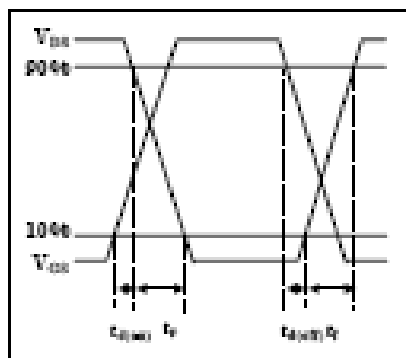


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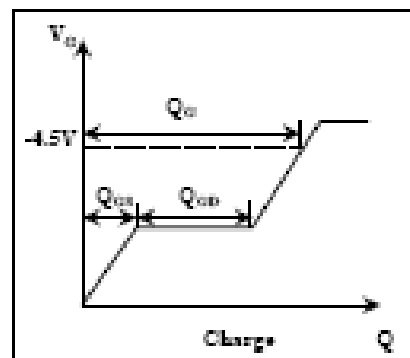
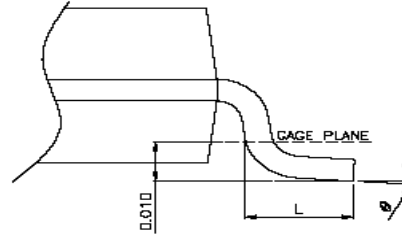
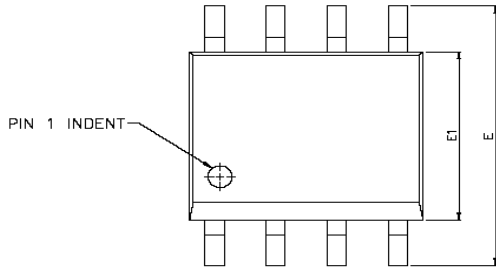


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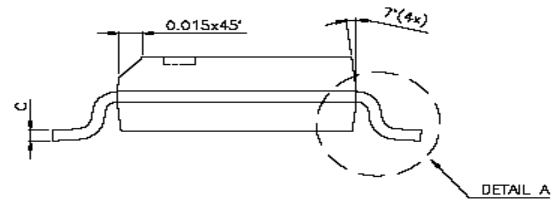
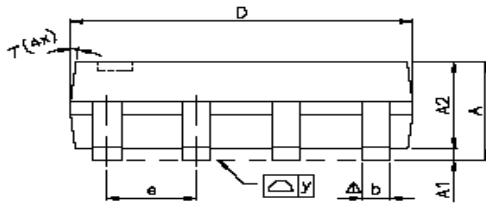


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SOP- 8 PACKAGE OUTLINE



DETAIL A



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	—	0.25	0.004	—	0.010
A2	—	1.45	—	—	0.057	—
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	—	1.27	—	—	0.050	—
L	0.38	0.71	1.27	0.015	0.028	0.050
Δ y	—	—	0.076	—	—	0.003
θ	0°	—	8°	0°	—	8°



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